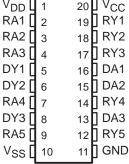
SLLS065F - AUGUST 1989 - REVISED JANUARY 2000

- Meets or Exceeds the Requirements of TIA/EIA-232-F and ITU Recommendation V 28
- Single Chip With Easy Interface Between UART and Serial-Port Connector
- Less Than 9-mW Power Consumption
- Wide Driver Supply Voltage . . . 4.5 V to 13.2 V
- Driver Output Slew Rate Limited to 30 V/us Max
- Receiver Input Hysteresis . . . 1100 mV Typ
- Push-Pull Receiver Outputs
- On-Chip Receiver 1-µs Noise Filter
- Functionally Interchangeable With Texas Instruments SN75185
- Operates Up to 120 kbit/s Over a 3-Meter Cable (See Application Information for Conditions)

(TOP VIEW) V_{DD} 1 20 V_{CC} RA1 2 19 RY1

DW OR N PACKAGE



description

The SN75C185 is a low-power BiMOS device containing three independent drivers and five receivers that are used to interface data terminal equipment (DTE) with data circuit-terminating equipment (DCE). Typically, the SN75C185 replaces one SN75188 and two SN75189 devices. This device conforms to TIA/EIA-232-F. The drivers and receivers of the SN75C185 are similar to those of the SN75C188 and SN75C189A, respectively. The drivers have a controlled output slew rate that is limited to a maximum of 30 V/ μ s, and the receivers have filters that reject input noise pulses that are shorter than 1 μ s. Both these features eliminate the need for external components.

The SN75C185 uses the low-power BiMOS technology. In most applications, the receivers contained in this device interface to single inputs of peripheral devices such as ACEs, UARTS, or microprocessors. By using sampling, such peripheral devices usually are insensitive to the transition times of the input signals. If this is not the case, or for other uses, it is recommended that the SN75C185 receiver outputs be buffered by single Schmitt input gates or single gates of the HCMOS, ALS, or 74F logic families.

The SN75C185 is characterized for operation from 0°C to 70°C.

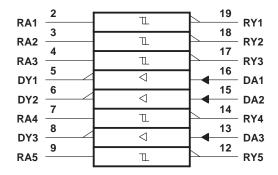


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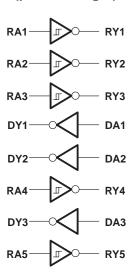
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logic symbol†



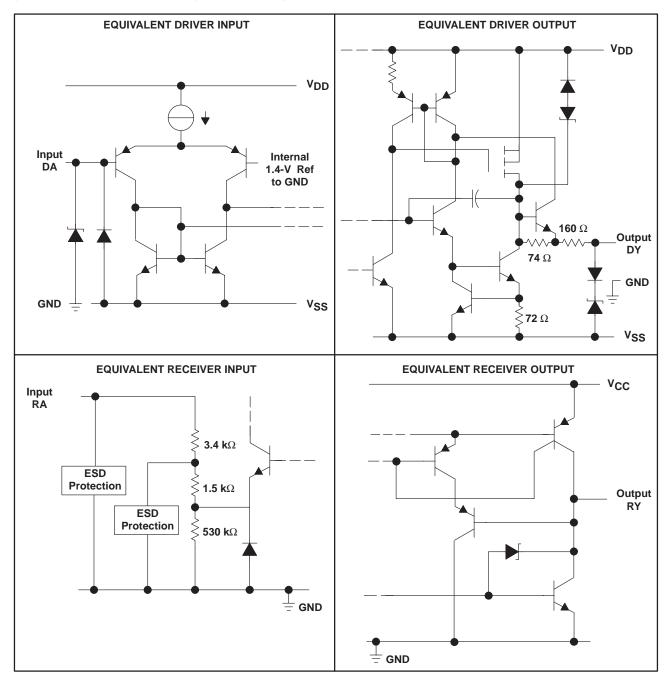
[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)





equivalent schematics of inputs and outputs



All resistor values are nominal.

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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage, V _{DD} (see Note 1)	13.5 V
Supply voltage, V _{SS}	
Supply voltage, V _{CC}	
Input voltage range, V _I : Driver	V _{SS} to V _{DD}
Receiver	30 V to 30 V
Output voltage range, VO: Driver	V_{SS} - 6 V to V_{DD} + 6 V
Receiver	$-0.3 \text{ V to V}_{CC} + 0.3 \text{ V}$
Package thermal impedance, θ_{JA} (see Note 2): DW package	58°C/W
N package	69°C/W
Operating free-air temperature range, T _A	0°C to 70°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C
Storage temperature range, T _{Stg}	65°C to 150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

recommended operating conditions

			MIN	NOM	MAX	UNIT
		V_{DD}	4.5	12	13.2	V
	Supply voltage	V _{SS}	-4.5	-12	-13.2	V
		VCC	4.5	5	6	V
٧,	Input voltage (eee Note 2)	Drivers	V _{SS} +2		V_{DD}	V
V _I Input voltage (see Note 3)		Receivers	-25		25	V
٧ _{IH}	High-level input voltage	Drivers	2			V
V_{IL}	Low-level input voltage	Dilveis			0.8	V
loh	High-level output current	Receivers			-1	mA
loL	OL High-level output current				3.2	mA
T _A	Operating free-air temperature		0	. The state of the	70	°C

NOTE 3: The algebraic convention, where the more positive (less negative) limit is designated as maximum, is used in this data sheet for logic levels only, e.g., if -10 V is a maximum, the typical value is a more negative voltage.

supply currents

	PARAMETER	TEST	MIN	TYP	MAX	UNIT		
1	Supply current from VDD	No load,	$V_{DD} = 5 V$,	$V_{SS} = -5 V$		115	200	
¹ DD	Зирріу сипені поні УДД	All inputs at 2 V or 0.8 V	V _{DD} = 12 V,	V _{SS} = -12 V		115	200	μΑ
laa	Supply ourrent from Voc	No load,	$V_{DD} = 5 V$,	$V_{SS} = -5 V$		-115	-200	
ISS	Supply current from VSS	All inputs at 2 V or 0.8 V	V _{DD} = 12 V,	V _{SS} = -12 V		-115	-200	μΑ
laa	Supply current from Voc	No load	$V_{DD} = 5 V$,	$V_{SS} = -5 \text{ V}$			750	μA
Icc	Supply current from V _{CC}	All inputs at 0 or 5 V	V _{DD} = 12 V,	$V_{SS} = -12 \text{ V}$			750	μΑ



NOTES: 1. All voltages are with respect to network GND.

^{2.} The package thermal impedance is calculated in accordance with JESD 51.

DRIVER SECTION

electrical characteristics over operating free-air temperature range, V_{DD} = 12 V, V_{SS} = –12 V, V_{CC} = 5 V $\pm 10\%$ (unless otherwise noted)

	PARAMETER		TEST C	ONDITIONS		MIN	TYP†	MAX	UNIT
Vou	High-level output voltage	V _{IL} = 0.8 V,	$R_L = 3 k\Omega$,	$V_{DD} = 5 V$,	$V_{SS} = -5 V$	4	4.5		V
VOH	r ligh-level output voltage	See Figure 1		V _{DD} = 12 V	$V_{SS} = -12 \text{ V}$	10	10.8		V
Voi	Low-level output voltage	V _{IH} = 0.8 V,	$R_L = 3 k\Omega$,	$V_{DD} = 5 V$,	$V_{SS} = -5 V$		-4.4	-4	V
VOL	(see Note 3)	See Figure 1		V _{DD} = 12 V	$V_{SS} = -12 \text{ V}$		-10.7	-10	V
lн	High-level input current	V _I = 5 V,	See Figure 2	2				1	μΑ
I _I L	Low-level input current	$V_{I} = 0$,	See Figure 2	2				-1	μΑ
IOS(H)	High-level short-circuit output current (see Note 4)	V _I = 0.8 V, See Flgure 1	$V_O = 0$ or V	o = V _{SS} ,		-4.5	-12	-19.5	mA
los(L)	Low-level short-circuit output current (see Note 4)	V _I = 2 V, See Figure 1	$V_O = 0$ or V	O = VDD,		4.5	12	19.5	mA
r _O	Output resistance	V _{DD} = V _{SS} = See Note 5	$V_{CC} = 0$,	$V_0 = -2 \text{ V to}$	2 V,	300	400	·	Ω

[†] All typical values are at $T_A = 25$ °C.

NOTES: 3. The algebraic convention, where the more positive (less negative) limit is designated as maximum, is used in this data sheet for logic levels only, e.g., if –10 V is a maximum, the typical value is a more negative voltage.

- 4. Not more than one output should be shorted at one time.
- 5. Test conditions are those specified by TIA/EIA-232-F.

switching characteristics, V_{DD} = 12 V, V_{SS} = -12 V, V_{CC} = 5 V ±10%, T_A = 25°C (unless otherwise noted) (see Figure 3)

	PARAMETER	TEST COND	DITIONS	MIN	TYP	MAX	UNIT
^t PLH	Propagation delay time, low- to high-level output (see Note 6)				1.2	3	μs
tPHL	Propagation delay time, high- to low-level output (see Note 6)	$R_L = 3 k\Omega$ to 7 kΩ,	C _L = 15 pF		2.5	3.5	μs
tTLH	Transition time, low- to high-level output			0.53	2	3.2	μs
tTHL	Transition time, high- to low-level output			0.53	2	3.2	μs
tTLH	Transition time, low- to high-level output (see Note 7)	$R_1 = 3 k\Omega \text{ to } 7 k\Omega$	C ₁ = 2500 pF		1		μs
tTHL	Transition time, high- to low-level output (see Note 7)	K[= 3 K22 to 7 K22,	CL = 2300 pr		1		μs
SR	Output slew rate (see Note 7)	$R_L = 3 \text{ k}\Omega \text{ to } 7 \text{ k}\Omega,$	C _L = 15 pF	4	10	30	V/µs

NOTES: 6. tpHL and tpLH include the additional time due to on-chip slew rate and are measured at the 50% points.

7. Measured between 3-V and -3-V points of output waveform TIA/EIA-232-F conditions), and all unused inputs are tied either high or low.



RECEIVER SECTION

electrical characteristics over operating free-air temperature range, V_{DD} = 12 V, V_{SS} = -12 V, V_{CC} = 5 V $\pm 10\%$ (unless otherwise noted)

	PARAMETER		TEST COND	TIONS	MIN	TYP [†]	MAX	UNIT
V _{IT+}	Positive-going input threshhold voltage	See Figure 5			1.6	2.1	2.55	V
VIT-	Negative-going input threshhold voltage	See Figure 5			0.65	1	1.25	٧
V _{hys}	Input hysteresis voltage (V _{IT+} - V _{IT-})				600	1100		mV
		V _I = 0.75 V,	$I_{OH} = -20 \mu A$,	See Figure 5 and Note 8	3.5			
\/a	High lovel output voltage	V _I = 0.75 V,	V _{CC} = 4.5 V		2.8	4.4		V
VOH	High-level output voltage	$I_{OH} = -1 \text{ mA},$	V _{CC} = 5 V		3.8	4.9		V
		See Figure 5	V _{CC} = 5.5 V		4.3	5.4		
VOL	Low-level output voltage	V _I = 3 V,	$I_{OL} = 3.2 \text{ mA},$	See Figure 5		0.17	0.4	V
1	High-level input current	V _I = 3 V			0.43	0.55	1	mA
¹IH	riign-ievei input current	V _I = 25 V			3.6	4.6	8.3	IIIA
1	Low lovel input current	V _I = −3 V			-0.43	-0.55	-1	mA
¹IL	Low-level input current	V _I = -25 V		·	-3.6	-5.0	-8.3	IIIA
IOS(H)	Short-circuit output at high level	V _I = 0.75 V,	V _O = 0,	See Figure 4		-8	-15	mA
I _{OS(L)}	Short-circuit output at low level	$V_I = V_{CC}$	$V_O = V_{CC}$	See Figure 4		13	25	mA

[†] All typical values are at T_A = 25 °C.

NOTE 8: If the inputs are left unconnected, the receiver interprets this as an input low, and the receiver outputs remain in the high state.

switching characteristics, V_{DD} = 12 V, V_{SS} = -12 V, V_{CC} = 5 V ±10%, T_A = 25°C (unless otherwise noted) (see Figure 6)

	PARAMETER	TEST CC	ONDITIONS	MIN	TYP	MAX	UNIT
tPLH	Propagation delay time, low- to high-level output				3	4	μs
tPHL	Propagation delay time, high- to low-level output	$R_1 = 5 k\Omega$	$C_{1} = 50 pF$		3	4	μs
^t TLH	Transition time, low- to high-level output	$K_{\perp} = 5 \text{ K}_{2}$	CL = 50 pr		300	450	ns
tTHL	Transition time, high- to low-level output				100	300	ns
t _{w(N)}	Duration of longest pulse rejected as noise (see Note 9)	$R_L = 5 k\Omega$,	C _L = 50 pF	1		4	μs

NOTE 9: The receiver ignores any postive- or negative-going pulse that is less than the minimum value of $t_{W(N)}$ and accepts any positive- or negative-going pulse greater than the maximum of $t_{W(N)}$.



PARAMETER MEASUREMENT INFORMATION

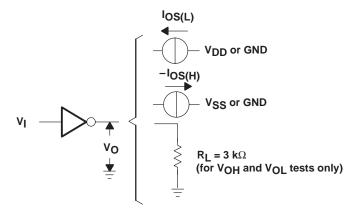


Figure 1. Driver Test Circuit for V_{OH} , V_{OL} , $I_{OS(H)}$, and $I_{OS(L)}$

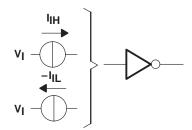
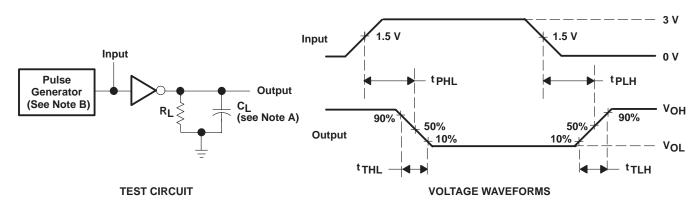


Figure 2. Driver Test Circuit for IIH and IIL



NOTES: A. C_L includes probe and jig capacitance.

B. The pulse generator has the following characteristics: t_W = 25 μ s, PRR = 20 kHz, Z_O = 50 Ω , t_f = t_f < 50 ns.

Figure 3. Driver Test Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION

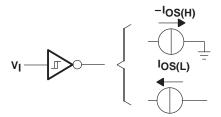


Figure 4. Receiver Test Circuit for I_{OS(H)} and I_{OS(L)}

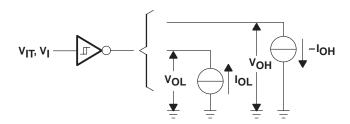
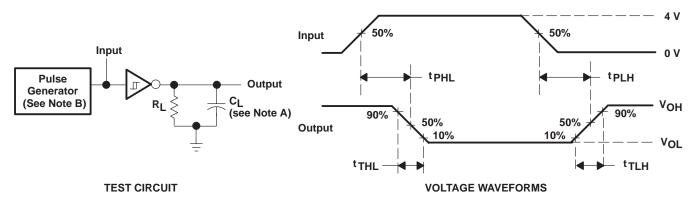


Figure 5. Receiver Test Circuit for V_{IT}, V_{OH}, and V_{OL}



NOTES: A. C_L includes probe and jig capacitance.

B. The pulse generator has the following characteristics: t_W = 25 μ s, PRR = 20 kHz, Z_O = 50 Ω , t_f = t_f < 50 ns.

Figure 6. Receiver Propagation and Transition Times



APPLICATION INFORMATION

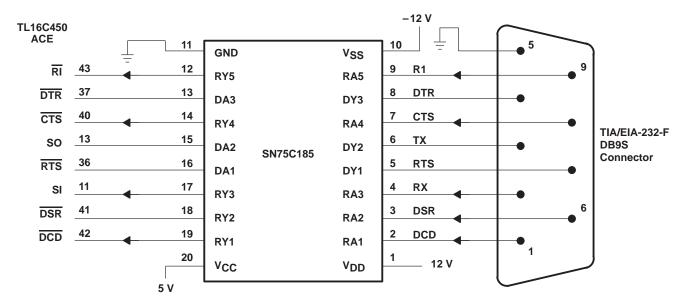
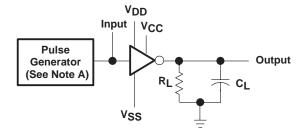


Figure 7. Typical Connection

The SN75C185 supports data rates up to 120 kbit/s over a 3-meter cable. Laboratory experiments show that, with C_L = 500 pF and R_L = 3 k Ω (minimum RS-232 input resistance load), the device can support this data rate. The 500-pF load approximates a typical 3-meter cable because the maximum RS-232 specification is 2500 pF (or about 15 meters). Figure 8 shows the test circuit used. Temperature was varied from 0°C to 70°C for the experiment.



NOTES: A. The pulse generator has the following characteristics: PRR = 60 kHz (120 kbit/s), $Z_O = 50 \Omega$.

B. $V_{CC} = 5 \text{ V}, V_{DD} = 12 \text{ V}, V_{SS} = -12 \text{ V}.$

Figure 8. Data-Rate Test Circuit

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
SN75C185DW	ACTIVE	SOIC	DW	20	25	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	SN75C185	Samples
SN75C185DWG4	ACTIVE	SOIC	DW	20	25	TBD	Call TI	Call TI	0 to 70		Samples
SN75C185DWR	ACTIVE	SOIC	DW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	SN75C185	Samples
SN75C185N	ACTIVE	PDIP	N	20	20	RoHS & Green	NIPDAU	N / A for Pkg Type	0 to 70	SN75C185N	Samples
SN75C185NE4	ACTIVE	PDIP	N	20	20	TBD	Call TI	Call TI	0 to 70		Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.



PACKAGE OPTION ADDENDUM

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

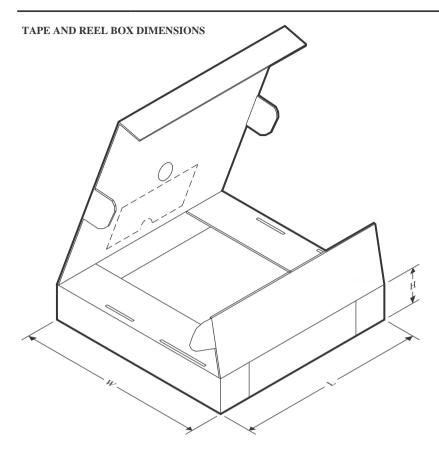


*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN75C185DWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1

PACKAGE MATERIALS INFORMATION

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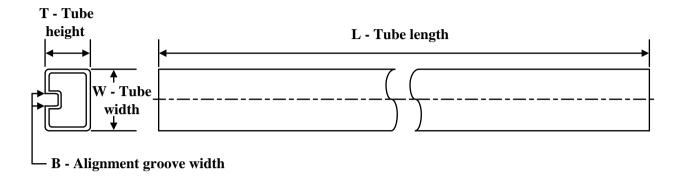
*All dimensions are nominal

Г	Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
Г	SN75C185DWR	SOIC	DW	20	2000	350.0	350.0	43.0

PACKAGE MATERIALS INFORMATION

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TUBE



*All dimensions are nominal

	Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
I	SN75C185DW	DW	SOIC	20	25	506.98	12.7	4826	6.6
ſ	SN75C185N	N	PDIP	20	20	506	13.97	11230	4.32

N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- The 20 pin end lead shoulder width is a vendor option, either half or full width.





SOIC



NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm per side.
- 5. Reference JEDEC registration MS-013.



SOIC



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOIC



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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